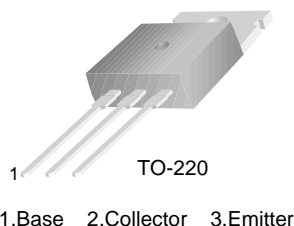


# BDW94/C

## PNP Epitaxial Silicon Transistor

### Power Linear and Switching Application

- Power Darlington TR
- Complement to BDW93 and BDW93C Respectively



### Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage		
	: BDW94	-45	V
	: BDW94C	-100	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: BDW94	-45	V
	: BDW94C	-100	V
I <sub>C</sub>	Collector Current (DC)	-12	A
I <sub>CP</sub>	Collector Current (Pulse) *	-15	A
I <sub>B</sub>	Base Current	-0.2	A
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> = 25°C)	80	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C

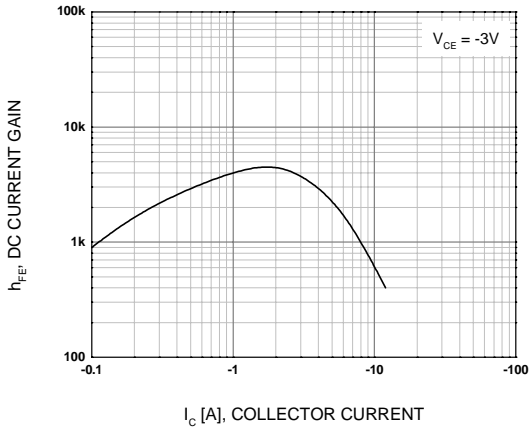
**Electrical Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
$V_{CE(sus)}$	Collector-Emitter Sustaining Voltage : BDW94 : BDW94C	$I_C = -100\text{mA}, I_B = 0$	-45 -100			V V
$I_{CBO}$	Collector Cut-off Current : BDW94 : BDW94C	$V_{CB} = -45\text{V}, I_E = 0$ $V_{CB} = -100\text{V}, I_E = 0$			-100 -100	$\mu\text{A}$ $\mu\text{A}$
$I_{CEO}$	Collector Cut-off Current : BDW94 : BDW94C	$V_{EB} = -45\text{V}, I_B = 0$ $V_{CE} = -100\text{V}, I_B = 0$			-1 -1	mA mA
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = -5\text{V}, I_C = 0$			-2	mA
$h_{FE}$	DC Current Gain *	$V_{CE} = -3\text{V}, I_C = -3\text{A}$ $V_{CE} = -3\text{V}, I_C = -5\text{A}$ $V_{CE} = -3\text{V}, I_C = -10\text{A}$	1000 750 100		20000	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage *	$I_C = -5\text{A}, I_B = -20\text{mA}$ $I_C = -10\text{A}, I_B = -100\text{mA}$			-2 -3	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage *	$I_C = -5\text{A}, I_B = -20\text{mA}$ $I_C = -10\text{A}, I_B = -100\text{mA}$			-2.5 -4	V V
$V_F$	Parallel Diode Forward Voltage *	$I_F = -5\text{A}$ $I_F = -10\text{A}$		-1.3 -1.8	-2 -4	V V

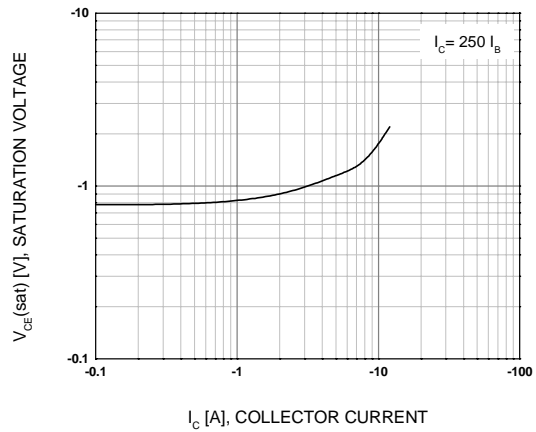
\* Pulse Test: PW = 300 $\mu\text{s}$ , Duty Cycle = 1.5% Pulsed

## Typical Performance Characteristics

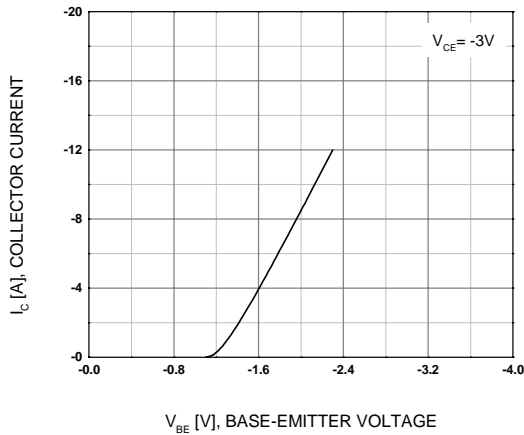
**Figure 1. DC Current Gain**



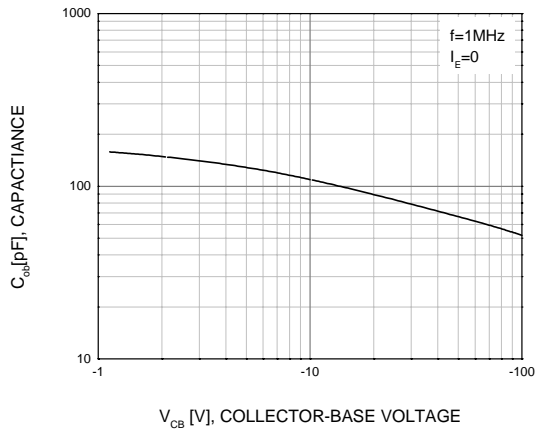
**Figure 2. Collector-Emitter Saturation Voltage**



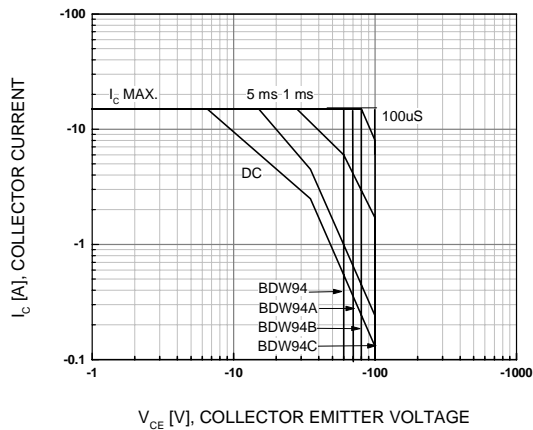
**Figure 3. Base-Emitter On Voltage**



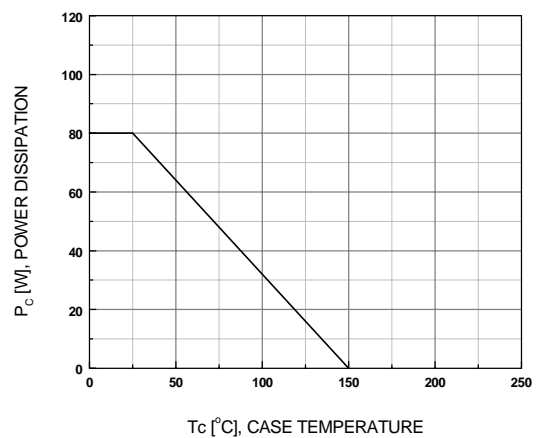
**Figure 4. Output Capacitance**



**Figure 5. Safe Operating Area**



**Figure 6. Power Derating**





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DOMET™	GTO™	MicroPak™	QFET®	SuperSOT™-8
EcoSPARK™	HiSeC™	MICROWIRE™	QS™	SyncFET™
E <sup>2</sup> CMOS™	I <sup>2</sup> C™	MSX™	QT Optoelectronics™	TinyLogic®
EnSigna™	i-Lo™	MSXPro™	Quiet Series™	TINYOPTO™
FACT™	ImpliedDisconnect™	OCX™	RapidConfigure™	TruTranslation™
FACT Quiet Series™		OCXPro™	RapidConnect™	UHC™
Across the board. Around the world.™		OPTOLOGIC®	μSerDes™	UltraFET®
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